

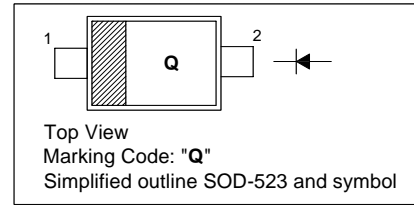
1SS413

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

for high speed switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

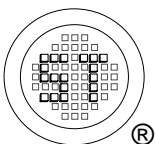


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V_R	20	V
Peak Forward Current	I_{FM}	100	mA
Average Forward Current	I_O	50	mA
Surge Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	100	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature	T_s	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 50\text{ mA}$	V_F	-	0.55	V
Reverse Current at $V_R = 20\text{ V}$	I_R	-	0.5	μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	3.9	-	pF



SEMTECH ELECTRONICS LTD.

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ISO/TS 16949 : 2002 Certificate No. 05103
ISO 14001:2004 Certificate No. 7116
ISO 9001:2000 Certificate No. 0506098

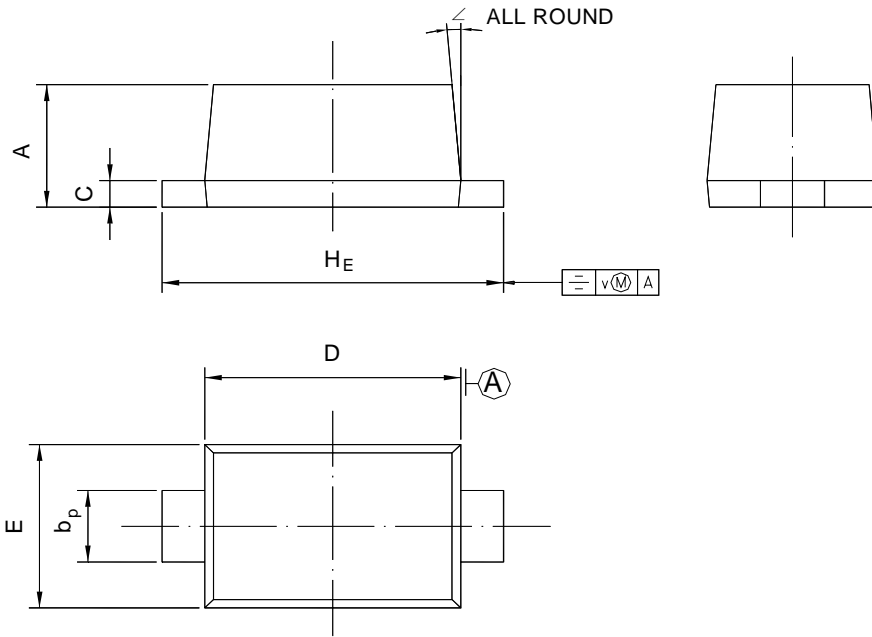
Dated : 23/11/2006

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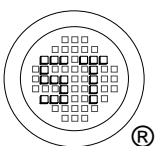
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.127	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°



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